



BDX18 – BDX18N

PNP SILICON TRANSISTOR EPITAXIAL BASE

LF Large Signal Power Amplification
High Current Switching

Suitable for :
Series and shunt regulators
High Fidelity Amplifiers
Power-switching circuits

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V_{CEO}	Collector-Emitter Voltage		BDX18 BDX18N	-60	V
V_{CER}	Collector-Emitter Voltage	$R_{BE}=100\Omega$	BDX18 BDX18N	-70 -65	V
V_{EBO}	Collector-Emitter Voltage		BDX18 BDX18N	-7	V
V_{CBO}	Emitter-Base Voltage		BDX18 BDX18N	-100 -70	V
V_{CEX}	Collector-Emitter Voltage	$V_{BE}=+1.5\text{ V}$	BDX18 BDX18N	-90 -70	V
I_C	Collector Current		BDX18 BDX18N	-15	A
I_B	Base Current		BDX18 BDX18N	-7	A
P_T	Power Dissipation	@ $T_C = 25^\circ$	BDX18 BDX18N	117	Watts
T_J	Junction Temperature		BDX18 BDX18N	-65 to +200	°C
T_S	Storage Temperature				

BDX18 – BDX18N

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	1.5	°C/W

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit	
$V_{CEO(SUS)}$	Collector-Emitter Breakdown Voltage (*)	$I_C=200\text{ mA}, I_B=0$	BDX18 BDX18N	-60 -60	-	-	V
$V_{CEX(SUS)}$	Collector-Emitter Breakdown Voltage (*)	$I_C=-100\text{ mA}, V_{BE}=1.5\text{ V}$	BDX18 BDX18N	-90 -70	-	-	V
$V_{CER(SUS)}$	Collector-Emitter Breakdown Voltage (*)	$I_C=-200\text{ mA}, R_{BE}=100\ \Omega$	BDX18 BDX18N	-70 -65	-	-	V
I_{CEX}	Collector-Emitter Cutoff Current	$V_{CE}=-90\text{ V}, V_{BE}=1.5\text{ V}$ $V_{CE}=-60\text{ V}, V_{BE}=1.5\text{ V}$ $T_{CASE}=150^\circ\text{C}$	BDX18	-	-	-5 -10	mA
		$V_{CE}=-70\text{ V}, V_{BE}=1.5\text{ V}$ $V_{CE}=-60\text{ V}, V_{BE}=1.5\text{ V}$ $T_{CASE}=150^\circ\text{C}$	BDX18N	-	-	-5 -10	
I_{EBO}	Emitter-Base Cutoff Current	$V_{EB}=-7\text{ V}$	BDX18 BDX18N	-	-	-5	mA
V_{BE}	Base-Emitter Voltage (*)	$I_C=-4.0\text{ A}, V_{CE}=-4.0\text{ V}$	BDX18 BDX18N	-	-	-1.8	V
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_C=-4.0\text{ A}, I_B=-0.4\text{ V}$	BDX18 BDX18N	-	-	-1.1	V
f_T	Transition Frequency	$I_C=-1\text{ A}, V_{CE}=-10\text{ V}, f=1\text{ MHz}$	BDX18 BDX18N	-	4	-	MHz

BDX18 – BDX18N

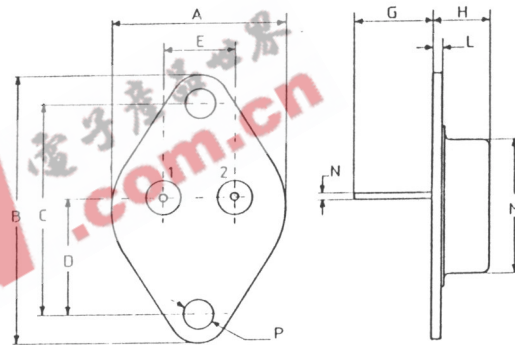
Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit
h_{21E}	Static Forward Current Transfer Ratio (*)	$V_{CE}=-4.0\text{ V}$, $I_C=-4.0\text{ A}$	20	-	70	-

(*) Pulse Width $\approx 300\ \mu\text{s}$, Duty Cycle $\angle 2.0\%$

(1) collector-Emitter voltage limited et $V_{CEci} = V_{\text{rated}}$ by an auxiliary circuit

MECHANICAL DATA CASE TO-3

DIMENSIONS		
	mm	inches
A	25,51	1,004
B	38,93	1,53
C	30,12	1,18
D	17,25	0,68
E	10,89	0,43
G	11,62	0,46
H	8,54	0,34
L	1,55	0,6
M	19,47	0,77
N	1	0,04
P	4,06	0,16



Pin 1 :	Base
Pin 2 :	Collector
Case :	Emitter